### IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

FB 17 200th at application of: Chiou et al.
Application Serial No.: 10/040,233

Med: November 7, 2001

For: Novel Design and Fabrication Method for Finger N-Type Doped

Photodiodes with High Sensitivity for CIS Products

Patent No.: Issue Date:

Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450 BEST AVAILABLE CO

# CERTIFICATE UNDER 37 C.F.R. §3.73(b) ESTABLISHING RIGHT OF ASSIGNEE TO TAKE ACTION

1. The assignee of the entire right, title and interest hereby seeks to take action in the PTO in this matter.

### **IDENTIFICATION OF ASSIGNEE**

2. The assignee of this matter is:

## TAIWAN SEMICONDUCTOR MANUFACTURING CO., LTD.

8, Li-Hsin Rd. 6 Hsinchu Science Park Hsinchu, Taiwan 300-77, R.O.C.

### PERSON AUTHORIZED TO SIGN

3. Daniel R. McClure Attorney for Assignee

# DEST AVAILABLE CO.

4.	A chain of title from the inventor(s) to the current assignee is shown below:					
	a.	From: Yu-Zung Chiou, Kuen-Hsien Lin, Chen Ying Lieh, Shou-Yi Hsu To: Taiwan Semiconductor Manufacturing Co., Ltd. Recorded in PTO: Reel: Frame:				
	b.	From: To: Recorded in PTO: Reel: Frame:				
·		Recorded in PTO: See Attached evidencing assignment that has already been filed. No Reel and Frame has been assigned as of yet.				
		<u>DECLARATIONS</u>				
5.	I, the undersigned, have reviewed all the documents in the chain of title of the					
		application patent				
matter identified abo		ove and, to the best of my knowledge and belief, title is in the assignee				
these statement are punishable	atemen nts are in e by find and that	by declare that all statements made herein of my own knowledge are true, its made on information and belief are believed to be true; and further, that made with the knowledge that willful false statements, and the like so made, ne or imprisonment, or both, under Section 1001, Title 18 of the United such willful false statements may jeopardize the validity of the application thereon.				
7. behalf of the		person signing below, aver that I am empowered to sign this statement one.				
Tel. No. 770 Customer No						

Docket No. 252016-1050

OWER OF STORNEY BY ASSIGNEE OF ENTIRE INTEREST
OF TRACE. (REVOCATION OF PRIOR POWERS)

As resource at accord at each of the patent applications listed in the table of attachment A.,

### REVOCATION OF PRIOR POWERS OF AUTORNEY

all powers of anomey previously given in each of the listed parent applications are hereby revoked, and

### NEW POWER OF ATTORNEY

Trademink Office connected therewith. Thereby appointed to prosecute this application and to transect all business in the Paters and Trademink Office connected therewith. Thereby appoint all attorneys of Thomas, Kayden, Harsterneyer & Rosley, LLP, who are assed under the USPTO Cosamuer Number shown below as the attorneys to prosecute this application and to transect all business in the United States Patent and Trademark Office connected therewith, recognizing that the specific attorneys listed under that Castorner Number may be changed from once to time at the sole discretion of Thomas, Kayden, Harsteineyer & Risley, LLP, and request that all correspondence about the application be addressed to the oddress filed under the state USPTO Customer Number.

24504 Patent Trademark Office

Please direct all finare correspondence and referbane cults to:

May 24 2004

Duniel R. McClure, Reg. No. 38,962
THOMAS, KAYDEN, HORSTEMEYER & RISLEY, L.L.F.
100 Galleria Purkway, Suite 1750
Adama, Georgia 30339
770-933-9500

#### ASSIGNEE OF ENTIRE INTEREST

TAIWAN SESHCONDUCTOR MANUFACTURING COMPANY, LTD.

8, Li-Hsin Rd. 6 Hsinchu Science Park Hsinchu, Taiwan 300-77, R.O.C

#### ASSIGNEE CERTIFICATION

the certification under 37 C.F.R. §5.73(b) establishing the right of assignce to take action is attached hereto along with documentation evidencing same. Further, in my official position with Taiwan Semiconductor Manufacturing Company. Ltd., I am authorized to sign documents and otherwise act on its behalf in connection with the management and handling of patent applications and other intellectual property matters.

1.745.4

Chien-Wei (Chris) Chou

Director - Intellectual Property Division

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No T	Serial No	TSMC No.	Application Title	Filing Date	Assignment
					(Reel/Frame)
****	10/120,834	TS1999705C	Process For High Voltage Oxide And Select Gate Poly For Split-Gate Flash Memory	4/11/2002	012791/0621
1	10/074,382	TS2000885	Methodology To Raduce The Early Failure Rate By Applying Dynamic Vottage Stressing in Testing With Screen Criteria Of Delta LSB	2/12/2002	012599/0197
1	19/933,961	TS20010325	Electrostatic Discharge-Free Container For Insulating Articles	8/22/2001	012128/0489
	10/053,473	TS20011053	Enhanced Adhesion Strength Between Mold Resin And Polyimide	1/28/2002	014216/0356
į	10/040,233	TS20010102	Novel Design And Fabrication Method For Finger N-Type Doped Photodicdes With High Sensitivity For CIS Products	11/7/2001	Filed 3-29-04 Copy anached
ģ	10/225,303	TS20010389	HDP Gap-Filling Process For Structures With Extra Step At Side- Wall	8/22/2002	913228/0267
manatan is orbi	10/679,737	TS20011380B	Method For Forming A Novel Top- Metal Fuse Structure	10/6/2003	012593/0150
8	10/437,092	TS200109968	Horizontal Surrounding Gate MOSFETS	5/13/2003	013368/0785
o o	10/338,738	TS20011442	Integrated High Performance MOS Tunneling Led in ULSI Technology	1/8/2003	013647/0832
10	10/177,912	TS20011051	Structure And Method For Low- Stress Concentration Solder Bumps	6/20/2002	013041/0230
¥,	10/313,501	TS20011509	Multivariate RBR Tool Aging Detector	12/6/2002	Copy attached
12	09/932,680	TS1998850/85 2BCC	Tilt-Angle Ion Implant To Improve Junction Breakdown in Flash Memory Application		010367/0646
13	C9/905,408	TS20010133	Selective Formation Of Metal Gate For Dual Fate Oxide Application	7/16/2001	012011/0342
14	10/288,194	TS20020083	Self-Aligned Structure With Unique Erasing Gate In Solit Gate Flash	11/8/2002	013483/0576
15	10/255,482	TS20020058	Method To Prevent Side Lobe On Seal Ring	9/26/2002	015341/0450
16	10/245,433	TS20011294	Metal Fuse For semiconductor devices	9/17/2002	

Date: Topay 24, 2004

She Wohn